

Silicon NPN Power Transistors

2SC3229

DESCRIPTION

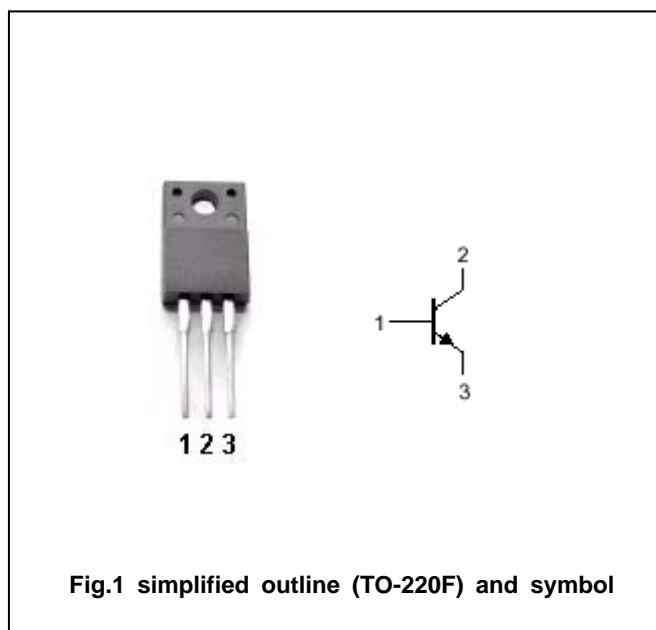
- With TO-220F package
- High voltage: $V_{CEO}=300V(\text{min})$

APPLICATIONS

- For color TV chroma output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		100	mA
I_B	Base current		20	mA
P_C	Collector power dissipation		2	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =10mA; I _B =1mA			1.0	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =100 μA; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10 μA; I _C =0	7			V
h _{FE-1}	DC current gain	I _C =0.5mA; V _{CE} =10V	20			
h _{FE-2}	DC current gain	I _C =20mA; V _{CE} =10V	30		200	
I _{CBO}	Collector cut-off current	V _{CB} =240V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	μA
C _{OB}	Output capacitance	I _E =0; V _{CB} =20V; f=1MHz			4.0	pF
f _T	Transition frequency	I _E =20mA; V _{CB} =20V	75			MHz

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PACKAGE OUTLINE

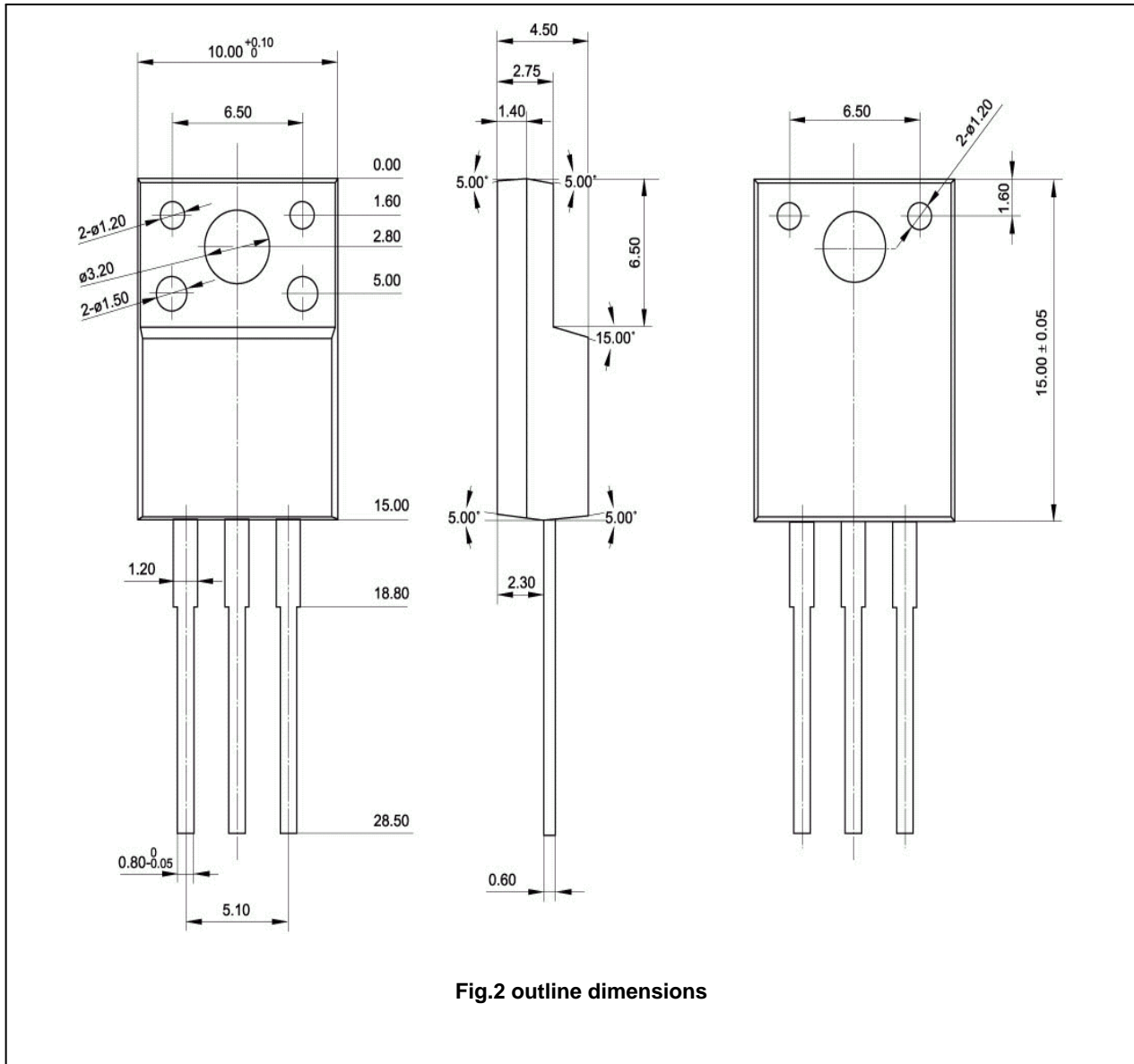


Fig.2 outline dimensions